

PROCEEDINGS OF SPIE

Optical and EUV Nanolithography XXXV

Anna Lio
Martin Burkhardt
Editors

24-28 April 2022
San Jose, California, United States

23-27 May 2022
ONLINE

Sponsored and Published by
SPIE

Volume 12051

Proceedings of SPIE 0277-786X, V. 12051

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Optical and EUV Nanolithography XXXV, edited by Anna Lio, Martin Burkhardt, Proc. of SPIE
Vol. 12051, 1205101 · © 2022 SPIE · 0277-786X · doi: 10.1117/12.2643342

Proc. of SPIE Vol. 12051 1205101-1

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Please use the following format to cite material from these proceedings:

Author(s), "Title of Paper," in *Optical and EUV Nanolithography XXXV*, edited by Anna Lio, Martin Burkhardt, Proc. of SPIE 12051, Seven-digit Article CID Number (DD/MM/YYYY); (DOI URL).

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510649774

ISBN: 9781510649781 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time)

SPIE.org

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